

N-CHANNEL MOS FIELD EFFECT TRANSISTOR FOR SWITCHING

DESCRIPTION

The μ PA1874B is a switching device, which can be driven directly by a 2.5 V power source.

The μ PA1874B features a low on-state resistance and excellent switching characteristics, and is suitable for applications such as power switch of portable machine and so on.

FEATURES

- 2.5 V drive available
- Low on-state resistance
 $R_{DS(on)1} = 14.0 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.5 \text{ V, } I_D = 4.0 \text{ A)}$
 $R_{DS(on)2} = 14.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 4.0 \text{ V, } I_D = 4.0 \text{ A)}$
 $R_{DS(on)3} = 16.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 3.1 \text{ V, } I_D = 4.0 \text{ A)}$
 $R_{DS(on)4} = 19.5 \text{ m}\Omega \text{ MAX. (} V_{GS} = 2.5 \text{ V, } I_D = 4.0 \text{ A)}$
- Built-in G-S protection diode against ESD

ORDERING INFORMATION

PART NUMBER	PACKAGE
μ PA1874BGR-9JG	Power TSSOP8

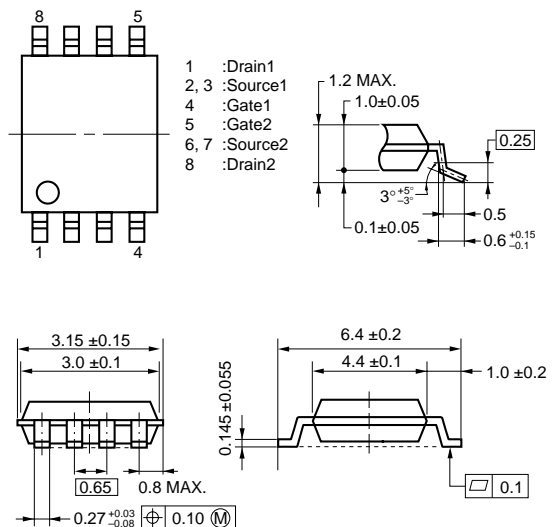
ABSOLUTE MAXIMUM RATINGS (T_A = 25°C)

Drain to Source Voltage (V _{GS} = 0 V)	V _{DSS}	30.0	V
Gate to Source Voltage (V _{DS} = 0 V)	V _{GSS}	±12.0	V
Drain Current (DC) ^{Note 1}	I _{D(DC)}	±8.0	A
Drain Current (pulse) ^{Note 2}	I _{D(pulse)}	±80.0	A
Total Power Dissipation ^{Note 1}	P _T	2.0	W
Channel Temperature	T _{ch}	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

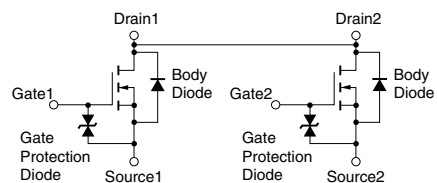
- Notes 1.** Mounted on ceramic board of 50 cm² x 1.1 mm
2. PW ≤ 10 μs, Duty Cycle ≤ 1%

Remark The diode connected between the gate and source of the transistor serves as a protector against ESD. When this device actually used, an additional protection circuit is externally required if a voltage exceeding the rated voltage may be applied to this device.

PACKAGE DRAWING (Unit: mm)



EQUIVALENT CIRCUIT



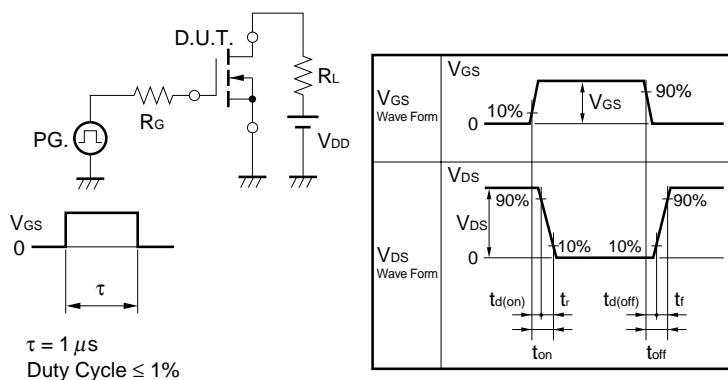
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ELECTRICAL CHARACTERISTICS (T_A = 25°C)

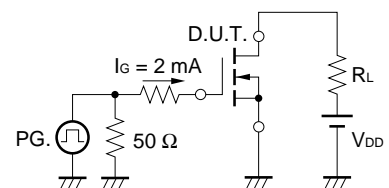
CHARACTERISTICS	SYMBOL	TEST CONDITIONS	MIN.	TYP.	MAX.	UNIT
Zero Gate Voltage Drain Current	I _{bss}	V _{DS} = 30.0 V, V _{GS} = 0 V			1.0	μA
Gate Leakage Current	I _{gss}	V _{GS} = ±12.0 V, V _{DS} = 0 V			±10.0	μA
Gate Cut-off Voltage	V _{GS(off)}	V _{DS} = 10.0 V, I _D = 1.0 mA	0.50	1.00	1.50	V
Forward Transfer Admittance Note	y _{fs}	V _{DS} = 10.0 V, I _D = 4.0 A	5			S
Drain to Source On-state Resistance Note	R _{DS(on)1}	V _{GS} = 4.5 V, I _D = 4.0 A	9.0	11.5	14.0	mΩ
	R _{DS(on)2}	V _{GS} = 4.0 V, I _D = 4.0 A	9.5	12.0	14.5	mΩ
	R _{DS(on)3}	V _{GS} = 3.1 V, I _D = 4.0 A	10.0	13.0	16.5	mΩ
	R _{DS(on)4}	V _{GS} = 2.5 V, I _D = 4.0 A	11.0	15.0	19.5	mΩ
Input Capacitance	C _{iss}	V _{DS} = 10.0 V		930		pF
Output Capacitance	C _{oss}	V _{GS} = 0 V		170		pF
Reverse Transfer Capacitance	C _{rss}	f = 1.0 MHz		120		pF
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10.0 V, I _D = 4.0 A		46		ns
Rise Time	t _r	V _{GS} = 4.0 V		230		ns
Turn-off Delay Time	t _{d(off)}	R _G = 10 Ω		260		ns
Fall Time	t _f			250		ns
Total Gate Charge	Q _G	V _{DD} = 24.0 V		10.0		nC
Gate to Source Charge	Q _{GS}	V _{GS} = 4.0 V		2.0		nC
Gate to Drain Charge	Q _{GD}	I _D = 8.0 A		4.5		nC
Body Diode Forward Voltage Note	V _{F(S-D)}	I _F = 8.0 A, V _{GS} = 0 V		0.82		V
Reverse Recovery Time	t _{rr}	I _F = 8.0 A, V _{GS} = 0 V		150		ns
Reverse Recovery Charge	Q _{rr}	di/dt = 50 A/μs		80		nC

Note Pulsed: PW ≤ 350 μs, Duty Cycle ≤ 2%

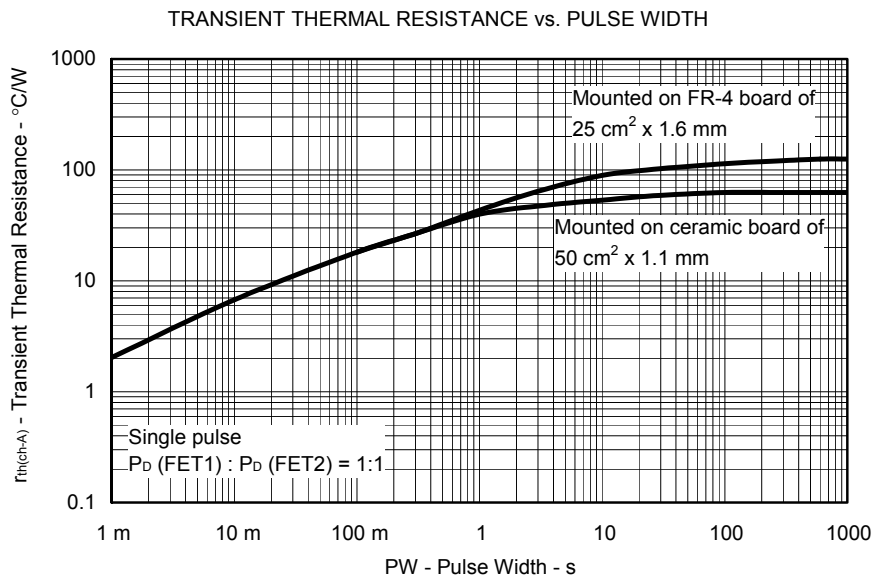
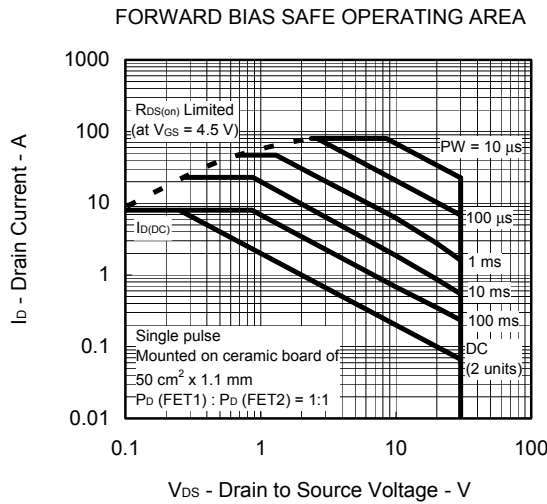
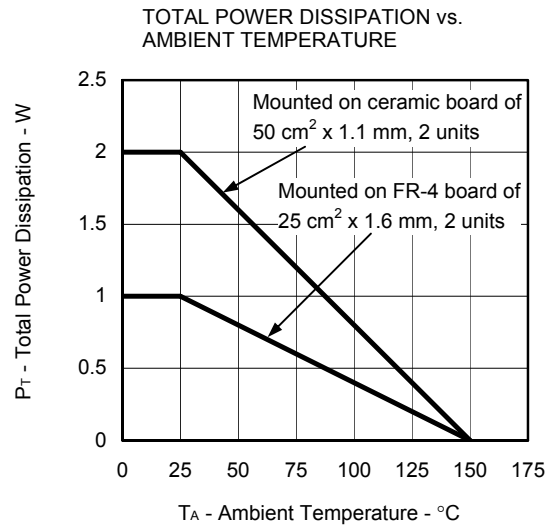
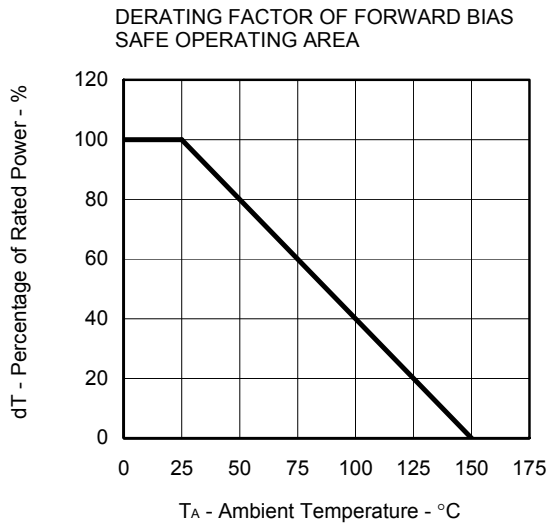
TEST CIRCUIT 1 SWITCHING TIME



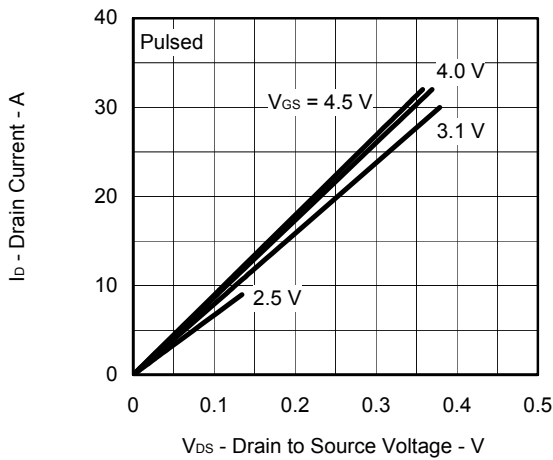
TEST CIRCUIT 2 GATE CHARGE



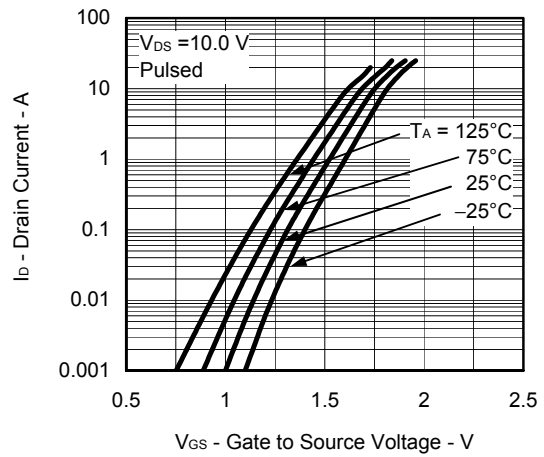
TYPICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$)



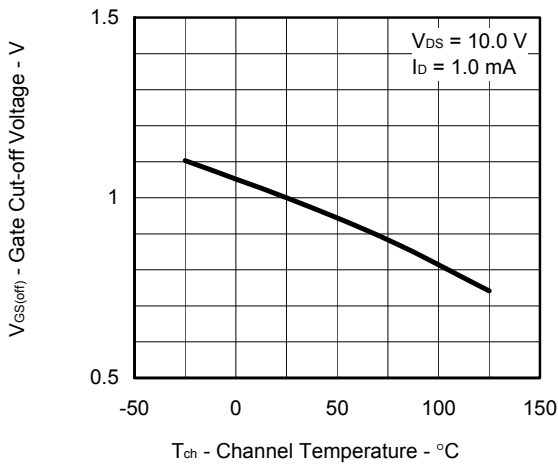
DRAIN CURRENT vs. DRAIN TO SOURCE VOLTAGE



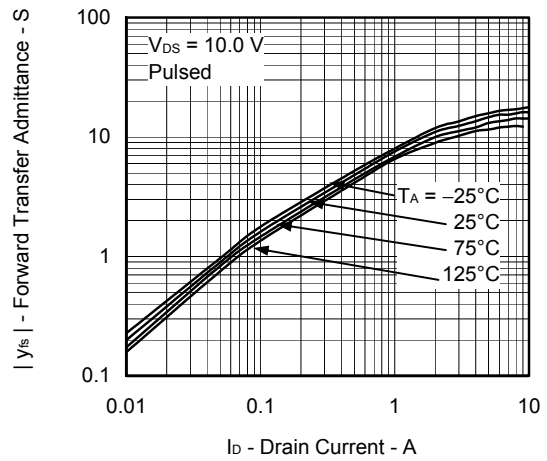
FORWARD TRANSFER CHARACTERISTICS



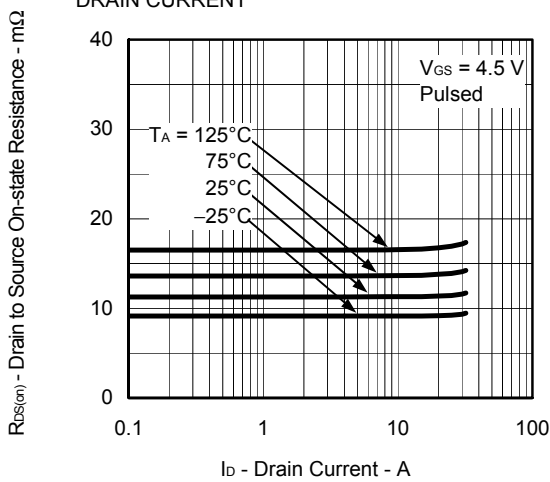
GATE CUT-OFF VOLTAGE vs. CHANNEL TEMPERATURE



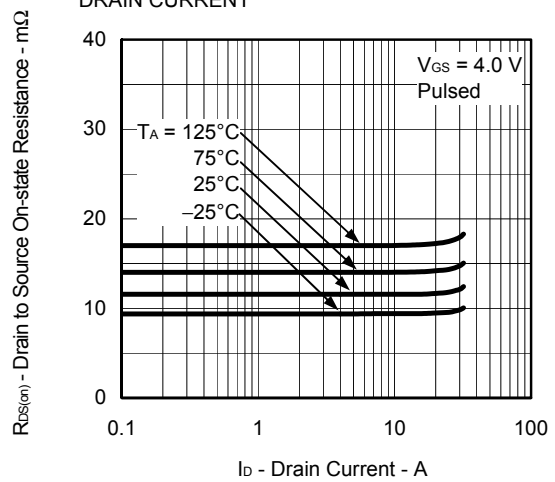
FORWARD TRANSFER ADMITTANCE vs. DRAIN CURRENT

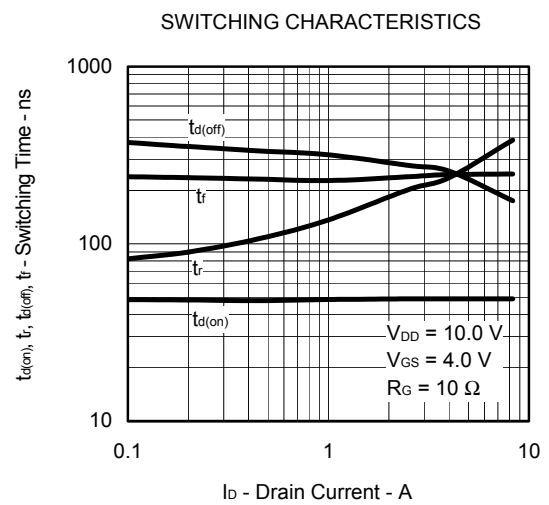
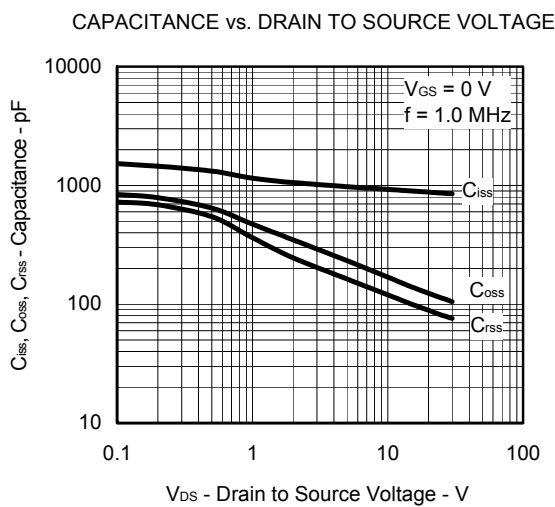
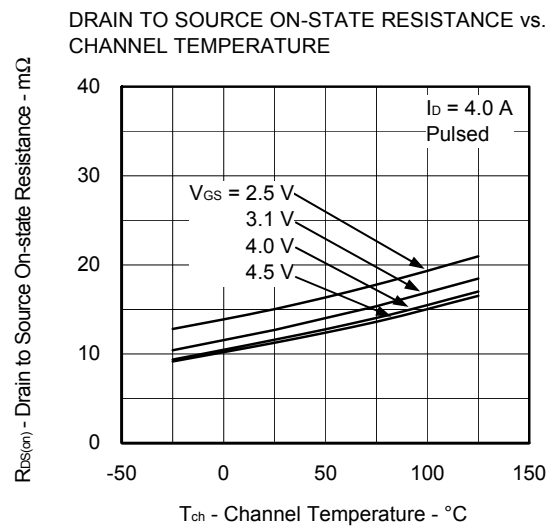
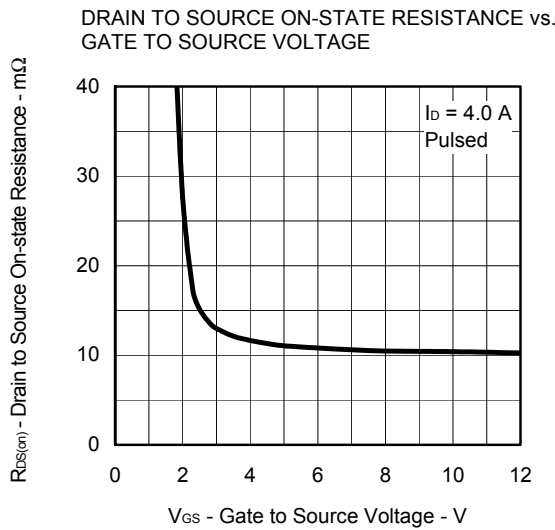
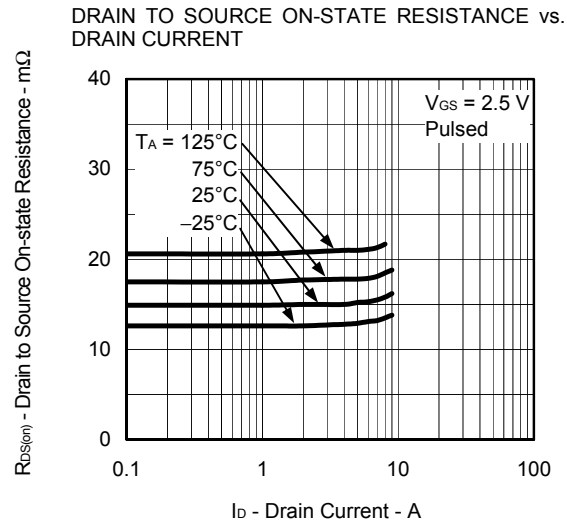
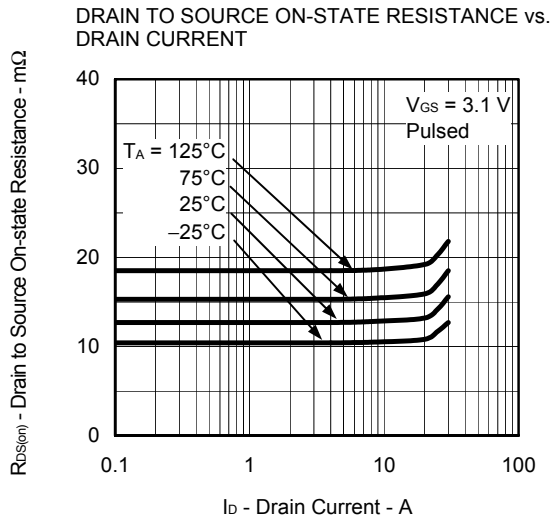


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

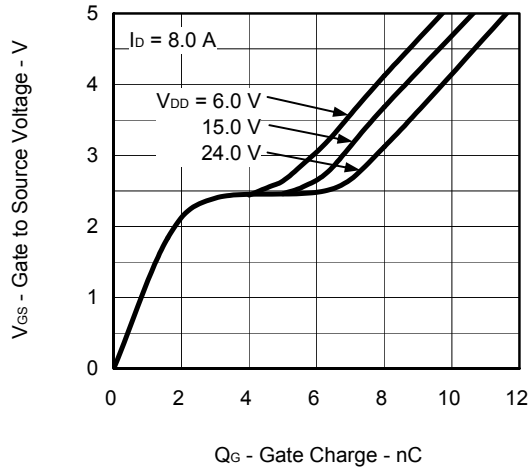


DRAIN TO SOURCE ON-STATE RESISTANCE vs. DRAIN CURRENT

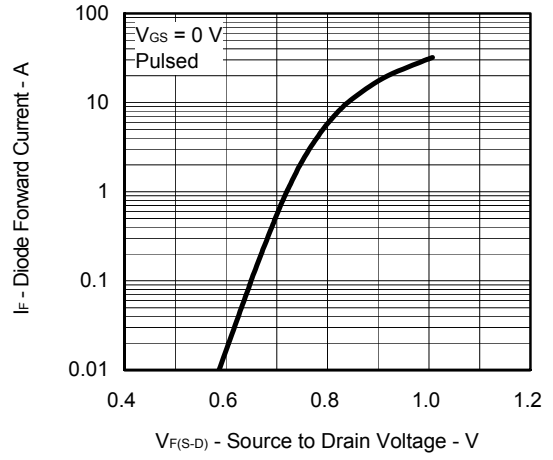




DYNAMIC INPUT CHARACTERISTICS



SOURCE TO DRAIN DIODE FORWARD VOLTAGE



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